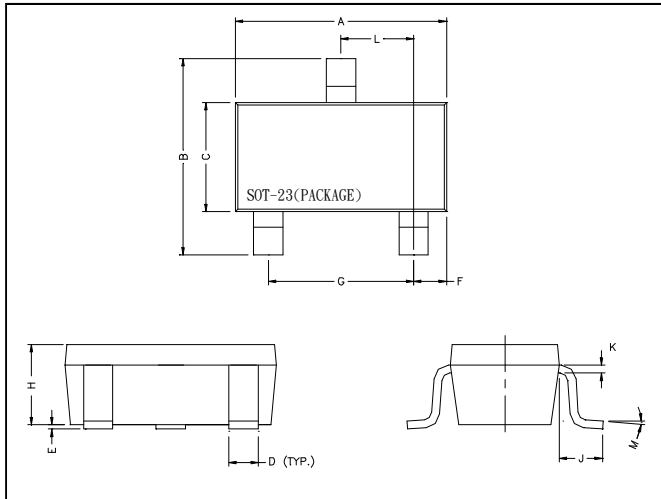


## GBAT54/A/C/S

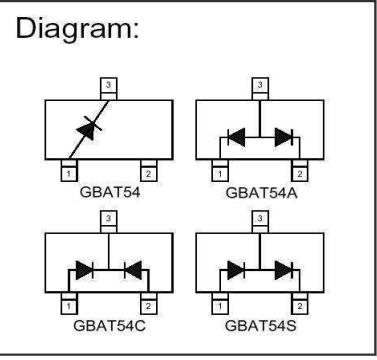
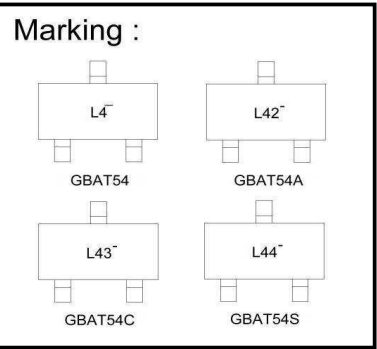
### Description

Silicon Schottky Barrier Double Diodes .

### Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°



Style : Pin 1.Anode 2.Cathode 3.Common Connection

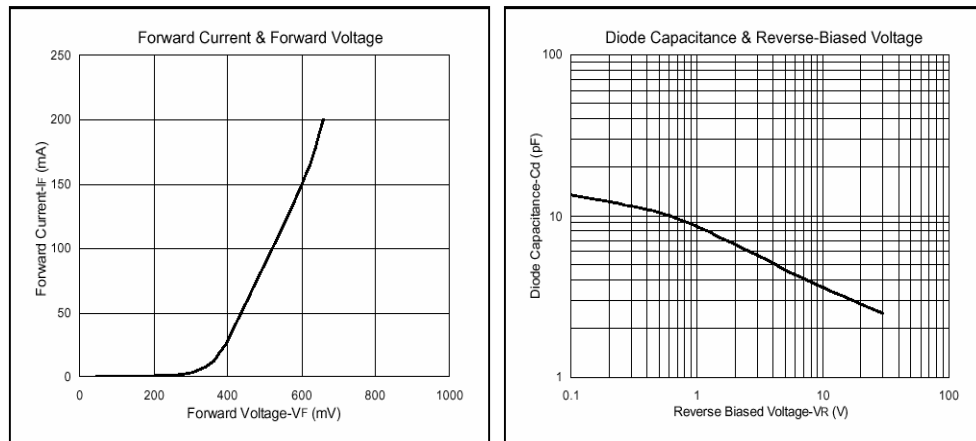
### Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Junction Temperature	T <sub>j</sub>	+125	°C
Storage Temperature	T <sub>stg</sub>	-65 ~ +125	°C
Repetitive Peak Reverse Voltage		30	V
Forward Continuous Current		200	mA
Repetitive Peak Forward Current		300	mA
Surge Forward Current		600	mA
Total Power Dissipation at Ta = 25°C	PD	230	mW

### Characteristics at Ta = 25°C

characteristics	Symbol	Min	Max.	Unit	Test Conditions
Reverse breakdown voltage	V(BR)R	30	-	V	IR=10uA
Forward Voltage	VF(1)	-	240	mV	IF=0.1mA
	VF(2)	-	320	mV	IF=1mA
	VF(3)	-	400	mV	IF=10mA
	VF(4)	-	500	mV	IF=30mA
	VF(5)	-	1000	mV	IF=100mA
Reverse Current	IR	-	2.0	uA	VR=25V
Total Capacitance	CT	-	10	pF	VR=1V, f=1MHz
Reverse Recover Time	T <sub>rr</sub>	-	5	ns	IF=IR=10mA, RL=100Ω measured at IR=1mA

## Characteristics Curve

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